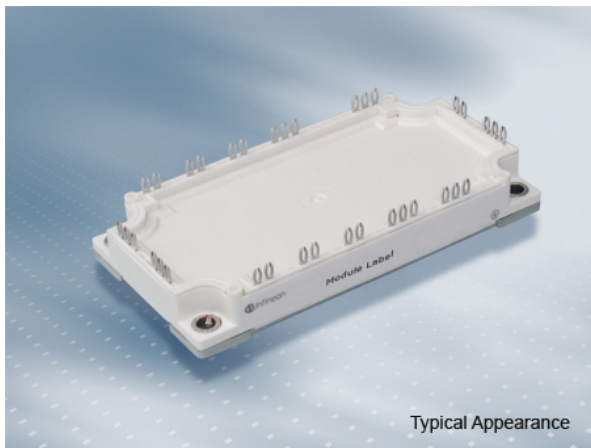
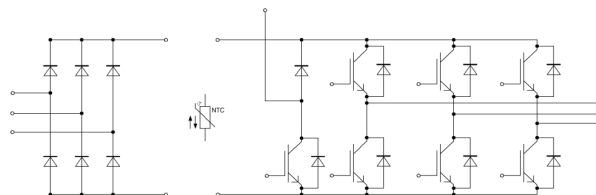


EconoPIM™3 模块 采用第四代沟槽栅/场终止IGBT4和发射极控制二极管 带有pressfit压接管脚和温度检测NTC  
EconoPIM™3 module with trench/fieldstop IGBT4 and Emitter Controlled Diode and PressFIT / NTC

初步数据 / Preliminary Data



Typical Appearance



$V_{CES} = 650V$

$I_{C\ nom} = 150A / I_{CRM} = 300A$

典型应用

- 电机传动

电气特性

- 增加阻断电压至650V
- 高短路能力，自限制短路电流
- 沟槽栅IGBT4
- $T_{vj\ op} = 150^{\circ}C$
- $V_{CESat}$  带正温度系数

机械特性

- 集成NTC温度传感器
- 铜基板
- PressFIT 压接技术
- 标封装

Typical Applications

- Motor Drives

Electrical Features

- Increased blocking voltage capability to 650V
- High Short Circuit Capability, Self Limiting Short Circuit Current
- Trench IGBT 4
- $T_{vj\ op} = 150^{\circ}C$
- $V_{CESat}$  with positive Temperature Coefficient

Mechanical Features

- Integrated NTC temperature sensor
- Copper Base Plate
- PressFIT Contact Technology
- Standard Housing

Module Label Code

Barcode Code 128



DMX - Code



Content of the Code

Digit

Module Serial Number	1 - 5
Module Material Number	6 - 11
Production Order Number	12 - 19
Datecode (Production Year)	20 - 21
Datecode (Production Week)	22 - 23

prepared by: AS	date of publication: 2013-11-05	
approved by: RS	revision: 2.0	UL approved (E83335)

初步数据  
Preliminary Data

IGBT, 逆变器 / IGBT, Inverter

最大额定值 / Maximum Rated Values

集电极 - 发射极电压 Collector-emitter voltage	$T_{vj} = 25^{\circ}\text{C}$	$V_{CES}$	650	V
连续集电极直流电流 Continuous DC collector current	$T_C = 55^{\circ}\text{C}, T_{vj\max} = 175^{\circ}\text{C}$	$I_{C\text{nom}}$	150	A
集电极重复峰值电流 Repetitive peak collector current	$t_P = 1\text{ms}$	$I_{CRM}$	300	A
总功率损耗 Total power dissipation	$T_C = 25^{\circ}\text{C}, T_{vj\max} = 175^{\circ}\text{C}$	$P_{\text{tot}}$	430	W
栅极 - 发射极峰值电压 Gate-emitter peak voltage		$V_{GES}$	+/-20	V

特征值 / Characteristic Values

			min.	typ.	max.		
集电极 - 发射极饱和电压 Collector-emitter saturation voltage	$I_C = 150\text{A}, V_{GE} = 15\text{V}$ $I_C = 150\text{A}, V_{GE} = 15\text{V}$ $I_C = 150\text{A}, V_{GE} = 15\text{V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$V_{CE\text{sat}}$	1,55 1,70 1,75	1,95	V V V	
栅极阈值电压 Gate threshold voltage	$I_C = 2,40\text{mA}, V_{CE} = V_{GE}, T_{vj} = 25^{\circ}\text{C}$		$V_{GEth}$	5,0	5,8	6,5	V
栅极电荷 Gate charge	$V_{GE} = -15\text{V} \dots +15\text{V}$		$Q_G$	1,50			$\mu\text{C}$
内部栅极电阻 Internal gate resistor	$T_{vj} = 25^{\circ}\text{C}$		$R_{Gint}$	2,0			$\Omega$
输入电容 Input capacitance	$f = 1\text{MHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{V}, V_{GE} = 0\text{V}$		$C_{ies}$	9,30			nF
反向传输电容 Reverse transfer capacitance	$f = 1\text{MHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{V}, V_{GE} = 0\text{V}$		$C_{res}$	0,285			nF
集电极-发射极截止电流 Collector-emitter cut-off current	$V_{CE} = 650\text{V}, V_{GE} = 0\text{V}, T_{vj} = 25^{\circ}\text{C}$		$I_{CES}$			1,0	mA
栅极-发射极漏电流 Gate-emitter leakage current	$V_{CE} = 0\text{V}, V_{GE} = 20\text{V}, T_{vj} = 25^{\circ}\text{C}$		$I_{GES}$			400	nA
开通延迟时间(电感负载) Turn-on delay time, inductive load	$I_C = 150\text{A}, V_{CE} = 300\text{V}$ $V_{GE} = \pm 15\text{V}$ $R_{Gon} = 3,3\Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$t_{d\text{on}}$	0,12 0,14 0,14			$\mu\text{s}$ $\mu\text{s}$ $\mu\text{s}$
上升时间(电感负载) Rise time, inductive load	$I_C = 150\text{A}, V_{CE} = 300\text{V}$ $V_{GE} = \pm 15\text{V}$ $R_{Gon} = 3,3\Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$t_r$	0,03 0,04 0,04			$\mu\text{s}$ $\mu\text{s}$ $\mu\text{s}$
关断延迟时间(电感负载) Turn-off delay time, inductive load	$I_C = 150\text{A}, V_{CE} = 300\text{V}$ $V_{GE} = \pm 15\text{V}$ $R_{Goff} = 3,3\Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$t_{d\text{off}}$	0,34 0,37 0,38			$\mu\text{s}$ $\mu\text{s}$ $\mu\text{s}$
下降时间(电感负载) Fall time, inductive load	$I_C = 150\text{A}, V_{CE} = 300\text{V}$ $V_{GE} = \pm 15\text{V}$ $R_{Goff} = 3,3\Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$t_f$	0,06 0,07 0,07			$\mu\text{s}$ $\mu\text{s}$ $\mu\text{s}$
开通损耗能量(每脉冲) Turn-on energy loss per pulse	$I_C = 150\text{A}, V_{CE} = 300\text{V}, L_S = 30\text{nH}$ $V_{GE} = \pm 15\text{V}, di/dt = 5400\text{A}/\mu\text{s} (T_{vj} = 150^{\circ}\text{C})$ $R_{Gon} = 3,3\Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$E_{\text{on}}$	0,94 1,50 1,65			mJ mJ mJ
关断损耗能量(每脉冲) Turn-off energy loss per pulse	$I_C = 150\text{A}, V_{CE} = 300\text{V}, L_S = 30\text{nH}$ $V_{GE} = \pm 15\text{V}, du/dt = 3800\text{V}/\mu\text{s} (T_{vj} = 150^{\circ}\text{C})$ $R_{Goff} = 3,3\Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$E_{\text{off}}$	5,75 7,40 7,85			mJ mJ mJ
短路数据 SC data	$V_{GE} \leq 15\text{V}, V_{CC} = 360\text{V}$ $V_{CE\text{max}} = V_{CES} - L_{SCE} \cdot di/dt$	$t_P \leq 10\mu\text{s}, T_{vj} = 25^{\circ}\text{C}$ $t_P \leq 10\mu\text{s}, T_{vj} = 150^{\circ}\text{C}$	$I_{SC}$	720 570			A A
结 - 外壳热阻 Thermal resistance, junction to case	每个 IGBT / per IGBT		$R_{thJC}$			0,35	K/W
外壳 - 散热器热阻 Thermal resistance, case to heatsink	每个 IGBT / per IGBT $\lambda_{\text{Paste}} = 1\text{W}/(\text{m}\cdot\text{K}) / \lambda_{\text{grease}} = 1\text{W}/(\text{m}\cdot\text{K})$		$R_{thCH}$			0,14	K/W
在开关状态下温度 Temperature under switching conditions			$T_{vj\text{op}}$	-40		150	$^{\circ}\text{C}$

prepared by: AS	date of publication: 2013-11-05
approved by: RS	revision: 2.0

初步数据  
Preliminary Data

二极管, 逆变器 / Diode, Inverter  
最大额定值 / Maximum Rated Values

反向重复峰值电压 Repetitive peak reverse voltage	$T_{vj} = 25^{\circ}\text{C}$	$V_{RRM}$	650	V
连续正向直流电流 Continuous DC forward current		$I_F$	150	A
正向重复峰值电流 Repetitive peak forward current	$t_p = 1\text{ ms}$	$I_{FRM}$	300	A
$I^2t$ -值 $I^2t$ - value	$V_R = 0\text{ V}, t_p = 10\text{ ms}, T_{vj} = 125^{\circ}\text{C}$ $V_R = 0\text{ V}, t_p = 10\text{ ms}, T_{vj} = 150^{\circ}\text{C}$	$I^2t$	2050 1950	$\text{A}^2\text{s}$ $\text{A}^2\text{s}$

特征值 / Characteristic Values

			min.	typ.	max.	
正向电压 Forward voltage	$I_F = 150\text{ A}, V_{GE} = 0\text{ V}$ $I_F = 150\text{ A}, V_{GE} = 0\text{ V}$ $I_F = 150\text{ A}, V_{GE} = 0\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$V_F$	1,55 1,50 1,45	1,95	V V V
反向恢复峰值电流 Peak reverse recovery current	$I_F = 150\text{ A}, -di_F/dt = 5400\text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$ $V_R = 300\text{ V}$ $V_{GE} = -15\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$I_{RM}$	150 180 185		A A A
恢复电荷 Recovered charge	$I_F = 150\text{ A}, -di_F/dt = 5400\text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$ $V_R = 300\text{ V}$ $V_{GE} = -15\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$Q_r$	7,00 13,0 15,0		$\mu\text{C}$ $\mu\text{C}$ $\mu\text{C}$
反向恢复损耗 (每脉冲) Reverse recovery energy	$I_F = 150\text{ A}, -di_F/dt = 5400\text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$ $V_R = 300\text{ V}$ $V_{GE} = -15\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$E_{rec}$	1,95 3,50 3,95		mJ mJ mJ
结 - 外壳热阻 Thermal resistance, junction to case	每个二极管 / per diode		$R_{thJC}$		0,60	K/W
外壳 - 散热器热阻 Thermal resistance, case to heatsink	每个二极管 / per diode $\lambda_{Paste} = 1\text{ W}/(\text{m}\cdot\text{K}) / \lambda_{grease} = 1\text{ W}/(\text{m}\cdot\text{K})$		$R_{thCH}$	0,245		K/W
在开关状态下温度 Temperature under switching conditions			$T_{vj\text{ op}}$	-40	150	$^{\circ}\text{C}$

二极管, 整流器 / Diode, Rectifier  
最大额定值 / Maximum Rated Values

反向重复峰值电压 Repetitive peak reverse voltage	$T_{vj} = 25^{\circ}\text{C}$	$V_{RRM}$	1600	V
最大正向均方根电流(每芯片) Maximum RMS forward current per chip	$T_C = 80^{\circ}\text{C}$	$I_{FRMSM}$	150	A
最大整流器输出均方根电流 Maximum RMS current at rectifier output	$T_C = 80^{\circ}\text{C}$	$I_{RMSM}$	150	A
正向浪涌电流 Surge forward current	$t_p = 10\text{ ms}, T_{vj} = 25^{\circ}\text{C}$ $t_p = 10\text{ ms}, T_{vj} = 150^{\circ}\text{C}$	$I_{FSM}$	1150 880	A A
$I^2t$ -值 $I^2t$ - value	$t_p = 10\text{ ms}, T_{vj} = 25^{\circ}\text{C}$ $t_p = 10\text{ ms}, T_{vj} = 150^{\circ}\text{C}$	$I^2t$	6600 3850	$\text{A}^2\text{s}$ $\text{A}^2\text{s}$

特征值 / Characteristic Values

			min.	typ.	max.	
正向电压 Forward voltage	$T_{vj} = 150^{\circ}\text{C}, I_F = 150\text{ A}$	$V_F$		1,10		V
反向电流 Reverse current	$T_{vj} = 150^{\circ}\text{C}, V_R = 1600\text{ V}$	$I_R$		1,00		mA
结 - 外壳热阻 Thermal resistance, junction to case	每个二极管 / per diode	$R_{thJC}$			0,40	K/W
外壳 - 散热器热阻 Thermal resistance, case to heatsink	每个二极管 / per diode $\lambda_{Paste} = 1\text{ W}/(\text{m}\cdot\text{K}) / \lambda_{grease} = 1\text{ W}/(\text{m}\cdot\text{K})$	$R_{thCH}$		0,165		K/W
在开关状态下温度 Temperature under switching conditions			$T_{vj\text{ op}}$	-40	150	$^{\circ}\text{C}$

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初步数据  
Preliminary Data

IGBT, 制动-斩波器 / IGBT, Brake-Chopper  
最大额定值 / Maximum Rated Values

集电极 - 发射极电压 Collector-emitter voltage	$T_{vj} = 25^{\circ}\text{C}$	$V_{CES}$	650	V
连续集电极直流电流 Continuous DC collector current	$T_C = 70^{\circ}\text{C}, T_{vj\max} = 175^{\circ}\text{C}$	$I_{C\text{nom}}$	100	A
集电极重复峰值电流 Repetitive peak collector current	$t_P = 1\text{ms}$	$I_{CRM}$	200	A
总功率损耗 Total power dissipation	$T_C = 25^{\circ}\text{C}, T_{vj\max} = 175^{\circ}\text{C}$	$P_{\text{tot}}$	335	W
栅极 - 发射极峰值电压 Gate-emitter peak voltage		$V_{GES}$	+/-20	V

特征值 / Characteristic Values

			min.	typ.	max.		
集电极 - 发射极饱和电压 Collector-emitter saturation voltage	$I_C = 100\text{A}, V_{GE} = 15\text{V}$ $I_C = 100\text{A}, V_{GE} = 15\text{V}$ $I_C = 100\text{A}, V_{GE} = 15\text{V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$V_{CE\text{sat}}$	1,55 1,70 1,75	1,95	V V V	
栅极阈值电压 Gate threshold voltage	$I_C = 1,60\text{mA}, V_{CE} = V_{GE}, T_{vj} = 25^{\circ}\text{C}$		$V_{GEth}$	5,0	5,8	6,5	V
栅极电荷 Gate charge	$V_{GE} = -15\text{V} \dots +15\text{V}$		$Q_G$	1,00			$\mu\text{C}$
内部栅极电阻 Internal gate resistor	$T_{vj} = 25^{\circ}\text{C}$		$R_{Gint}$	2,0			$\Omega$
输入电容 Input capacitance	$f = 1\text{MHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{V}, V_{GE} = 0\text{V}$		$C_{ies}$	6,20			nF
反向传输电容 Reverse transfer capacitance	$f = 1\text{MHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{V}, V_{GE} = 0\text{V}$		$C_{res}$	0,19			nF
集电极-发射极截止电流 Collector-emitter cut-off current	$V_{CE} = 650\text{V}, V_{GE} = 0\text{V}, T_{vj} = 25^{\circ}\text{C}$		$I_{CES}$			1,0	mA
栅极-发射极漏电流 Gate-emitter leakage current	$V_{CE} = 0\text{V}, V_{GE} = 20\text{V}, T_{vj} = 25^{\circ}\text{C}$		$I_{GES}$			400	nA
开通延迟时间(电感负载) Turn-on delay time, inductive load	$I_C = 100\text{A}, V_{CE} = 300\text{V}$ $V_{GE} = \pm 15\text{V}$ $R_{Gon} = 3,3\Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$t_{d\text{on}}$	0,07 0,08 0,08			$\mu\text{s}$ $\mu\text{s}$ $\mu\text{s}$
上升时间(电感负载) Rise time, inductive load	$I_C = 100\text{A}, V_{CE} = 300\text{V}$ $V_{GE} = \pm 15\text{V}$ $R_{Gon} = 3,3\Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$t_r$	0,02 0,02 0,02			$\mu\text{s}$ $\mu\text{s}$ $\mu\text{s}$
关断延迟时间(电感负载) Turn-off delay time, inductive load	$I_C = 100\text{A}, V_{CE} = 300\text{V}$ $V_{GE} = \pm 15\text{V}$ $R_{Goff} = 3,3\Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$t_{d\text{off}}$	0,26 0,29 0,30			$\mu\text{s}$ $\mu\text{s}$ $\mu\text{s}$
下降时间(电感负载) Fall time, inductive load	$I_C = 100\text{A}, V_{CE} = 300\text{V}$ $V_{GE} = \pm 15\text{V}$ $R_{Goff} = 3,3\Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$t_f$	0,07 0,07 0,07			$\mu\text{s}$ $\mu\text{s}$ $\mu\text{s}$
开通损耗能量(每脉冲) Turn-on energy loss per pulse	$I_C = 100\text{A}, V_{CE} = 300\text{V}, L_S = 30\text{nH}$ $V_{GE} = \pm 15\text{V}, di/dt = 5100\text{A}/\mu\text{s} (T_{vj} = 150^{\circ}\text{C})$ $R_{Gon} = 3,3\Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$E_{\text{on}}$	0,33 0,77 0,88			mJ mJ mJ
关断损耗能量(每脉冲) Turn-off energy loss per pulse	$I_C = 100\text{A}, V_{CE} = 300\text{V}, L_S = 30\text{nH}$ $V_{GE} = \pm 15\text{V}, du/dt = 4000\text{V}/\mu\text{s} (T_{vj} = 150^{\circ}\text{C})$ $R_{Goff} = 3,3\Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$E_{\text{off}}$	3,50 4,70 4,90			mJ mJ mJ
短路数据 SC data	$V_{GE} \leq 15\text{V}, V_{CC} = 360\text{V}$ $V_{CE\text{max}} = V_{CES} - L_{SCE} \cdot di/dt$	$t_P \leq 10\mu\text{s}, T_{vj} = 25^{\circ}\text{C}$ $t_P \leq 10\mu\text{s}, T_{vj} = 150^{\circ}\text{C}$	$I_{SC}$	480 380			A A
结 - 外壳热阻 Thermal resistance, junction to case	每个 IGBT / per IGBT		$R_{thJC}$			0,45	K/W
外壳 - 散热器热阻 Thermal resistance, case to heatsink	每个 IGBT / per IGBT $\lambda_{\text{Paste}} = 1\text{W}/(\text{m}\cdot\text{K}) / \lambda_{\text{grease}} = 1\text{W}/(\text{m}\cdot\text{K})$		$R_{thCH}$			0,185	K/W
在开关状态下温度 Temperature under switching conditions			$T_{vj\text{op}}$	-40		150	$^{\circ}\text{C}$

prepared by: AS	date of publication: 2013-11-05
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初步数据  
Preliminary Data

二极管，制动-斩波器 / Diode, Brake-Chopper  
最大额定值 / Maximum Rated Values

反向重复峰值电压 Repetitive peak reverse voltage	$T_{vj} = 25^{\circ}\text{C}$	$V_{RRM}$	650	V
连续正向直流电流 Continuous DC forward current		$I_F$	50	A
正向重复峰值电流 Repetitive peak forward current	$t_P = 1\text{ ms}$	$I_{FRM}$	100	A
$I^2t$ -值 $I^2t$ - value	$V_R = 0\text{ V}, t_P = 10\text{ ms}, T_{vj} = 125^{\circ}\text{C}$	$I^2t$	330	$\text{A}^2\text{s}$
	$V_R = 0\text{ V}, t_P = 10\text{ ms}, T_{vj} = 150^{\circ}\text{C}$		300	$\text{A}^2\text{s}$

特征值 / Characteristic Values

			min.	typ.	max.	
正向电压 Forward voltage	$I_F = 50\text{ A}, V_{GE} = 0\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$		1,55	1,95	V
	$I_F = 50\text{ A}, V_{GE} = 0\text{ V}$	$T_{vj} = 125^{\circ}\text{C}$	$V_F$	1,50		V
	$I_F = 50\text{ A}, V_{GE} = 0\text{ V}$	$T_{vj} = 150^{\circ}\text{C}$		1,45		V
反向恢复峰值电流 Peak reverse recovery current	$I_F = 50\text{ A}, -di_F/dt = 2800\text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$ $V_R = 300\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$		69,0		A
		$T_{vj} = 125^{\circ}\text{C}$	$I_{RM}$	76,0		A
		$T_{vj} = 150^{\circ}\text{C}$		80,0		A
恢复电荷 Recovered charge	$I_F = 50\text{ A}, -di_F/dt = 2800\text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$ $V_R = 300\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$		1,90		$\mu\text{C}$
		$T_{vj} = 125^{\circ}\text{C}$	$Q_r$	3,40		$\mu\text{C}$
		$T_{vj} = 150^{\circ}\text{C}$		3,95		$\mu\text{C}$
反向恢复损耗 (每脉冲) Reverse recovery energy	$I_F = 50\text{ A}, -di_F/dt = 2800\text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$ $V_R = 300\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$		0,60		mJ
		$T_{vj} = 125^{\circ}\text{C}$	$E_{rec}$	0,95		mJ
		$T_{vj} = 150^{\circ}\text{C}$		1,10		mJ
结 - 外壳热阻 Thermal resistance, junction to case	每个二极管 / per diode	$R_{thJC}$			1,20	K/W
外壳 - 散热器热阻 Thermal resistance, case to heatsink	每个二极管 / per diode $\lambda_{Paste} = 1\text{ W}/(\text{m}\cdot\text{K}) / \lambda_{grease} = 1\text{ W}/(\text{m}\cdot\text{K})$	$R_{thCH}$		0,49		K/W
在开关状态下温度 Temperature under switching conditions		$T_{vj op}$	-40		150	$^{\circ}\text{C}$

负温度系数热敏电阻 / NTC-Thermistor

特征值 / Characteristic Values

			min.	typ.	max.	
额定电阻值 Rated resistance	$T_C = 25^{\circ}\text{C}$	$R_{25}$		5,00		$\text{k}\Omega$
R100 偏差 Deviation of R100	$T_C = 100^{\circ}\text{C}, R_{100} = 493\ \Omega$	$\Delta R/R$	-5		5	%
耗散功率 Power dissipation	$T_C = 25^{\circ}\text{C}$	$P_{25}$			20,0	mW
B-值 B-value	$R_2 = R_{25} \exp [B_{25/50}(1/T_2 - 1/(298,15\text{ K}))]$	$B_{25/50}$		3375		K
B-值 B-value	$R_2 = R_{25} \exp [B_{25/80}(1/T_2 - 1/(298,15\text{ K}))]$	$B_{25/80}$		3411		K
B-值 B-value	$R_2 = R_{25} \exp [B_{25/100}(1/T_2 - 1/(298,15\text{ K}))]$	$B_{25/100}$		3433		K

根据应用手册标定

Specification according to the valid application note.

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初步数据  
Preliminary Data

模块 / Module

绝缘测试电压 Isolation test voltage	RMS, f = 50 Hz, t = 1 min.	V <sub>ISOL</sub>	2,5		kV
模块基板材料 Material of module baseplate			Cu		
内部绝缘 Internal isolation	基本绝缘 (class 1, IEC 61140) basic insulation (class 1, IEC 61140)		Al <sub>2</sub> O <sub>3</sub>		
爬电距离 Creepage distance	端子- 散热片 / terminal to heatsink 端子- 端子 / terminal to terminal		10,0		mm
电气间隙 Clearance	端子- 散热片 / terminal to heatsink 端子- 端子 / terminal to terminal		7,5		mm
相对电痕指数 Comperative tracking index		CTI	> 200		
			min.	typ.	max.
外壳 - 散热器热阻 Thermal resistance, case to heatsink	每个模块 / per module $\lambda_{\text{Paste}} = 1 \text{ W/(m}\cdot\text{K)} / \lambda_{\text{grease}} = 1 \text{ W/(m}\cdot\text{K)}$	R <sub>thCH</sub>	0,009		K/W
杂散电感,模块 Stray inductance module		L <sub>sCE</sub>	40		nH
模块引线电阻,端子-芯片 Module lead resistance, terminals - chip	T <sub>C</sub> = 25°C, 每个开关 / per switch	R <sub>CC'+EE'</sub> R <sub>AA'+CC'</sub>	4,00 2,00		mΩ
最大结温 Maximum junction temperature	逆变器,制动-斩波器 / inverter, brake-chopper 整流器 / rectifier	T <sub>vj max</sub>			175 °C 150 °C
在开关状态下温度 Temperature under switching conditions	逆变器,制动-斩波器 / inverter, brake-chopper 整流器 / rectifier	T <sub>vj op</sub>	-40 -40		150 °C 150 °C
储存温度 Storage temperature		T <sub>stg</sub>	-40		125 °C
模块安装的安装扭矩 Mounting torque for modul mounting	螺丝 M5 根据相应的应用手册进行安装 Screw M5 - Mounting according to valid application note	M	3,00	-	6,00 Nm
重量 Weight		G	300		g

bei Betrieb mit V<sub>ge</sub> = 0V/+15V empfehlen wir einen R<sub>gon,min</sub> von 24 Ohm und eine R<sub>goff,min</sub> von 24 Ohm (siehe AN 2006-01)  
for operation with V<sub>ge</sub>= 0V/+15V we recommend a R<sub>gon,min</sub> of 24 ohms and a R<sub>goff,min</sub> of 24 ohms (see AN 2006-01)

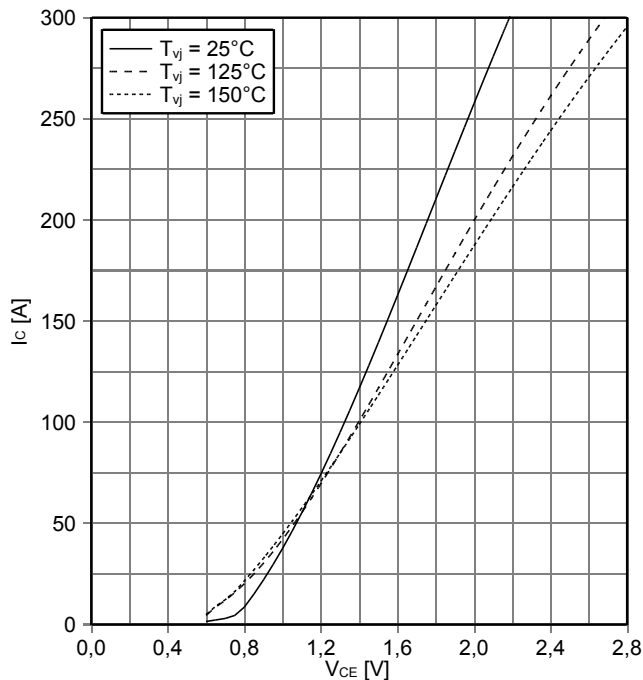
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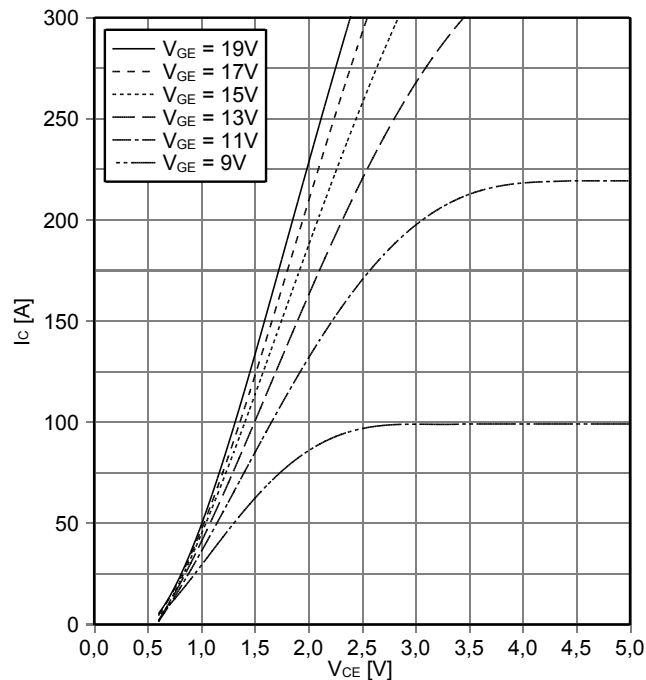
输出特性 IGBT, 逆变器 (典型)  
output characteristic IGBT, Inverter (typical)

$I_C = f(V_{CE})$   
 $V_{GE} = 15\text{ V}$



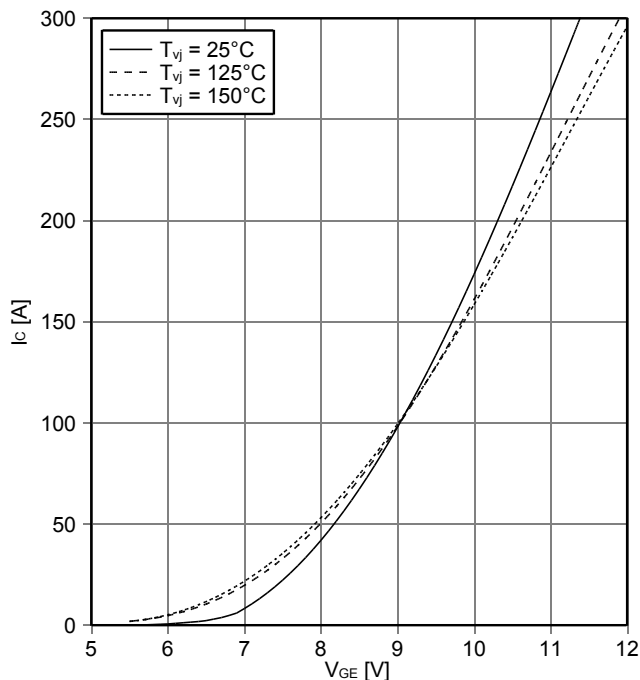
输出特性 IGBT, 逆变器 (典型)  
output characteristic IGBT, Inverter (typical)

$I_C = f(V_{CE})$   
 $T_{vj} = 150^\circ\text{C}$



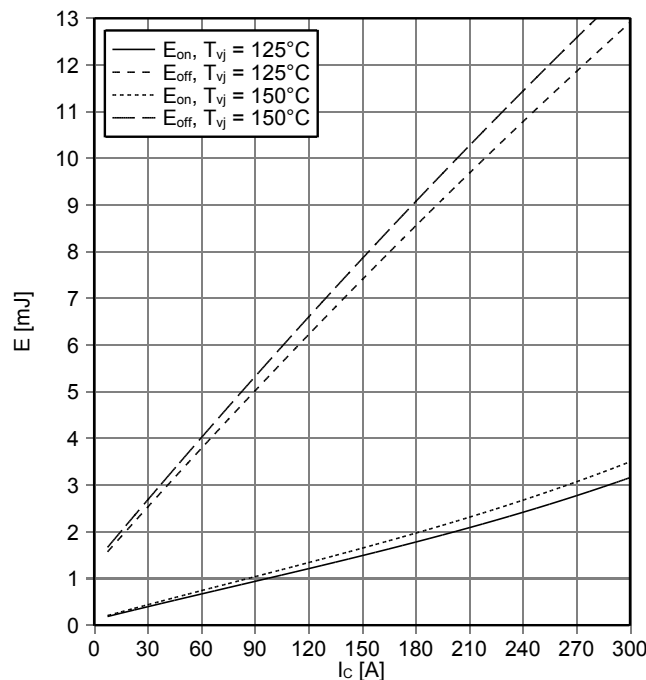
传输特性 IGBT, 逆变器 (典型)  
transfer characteristic IGBT, Inverter (typical)

$I_C = f(V_{GE})$   
 $V_{CE} = 20\text{ V}$



开关损耗 IGBT, 逆变器 (典型)  
switching losses IGBT, Inverter (typical)

$E_{on} = f(I_C)$ ,  $E_{off} = f(I_C)$   
 $V_{GE} = \pm 15\text{ V}$ ,  $R_{Gon} = 3.3\ \Omega$ ,  $R_{Goff} = 3.3\ \Omega$ ,  $V_{CE} = 300\text{ V}$

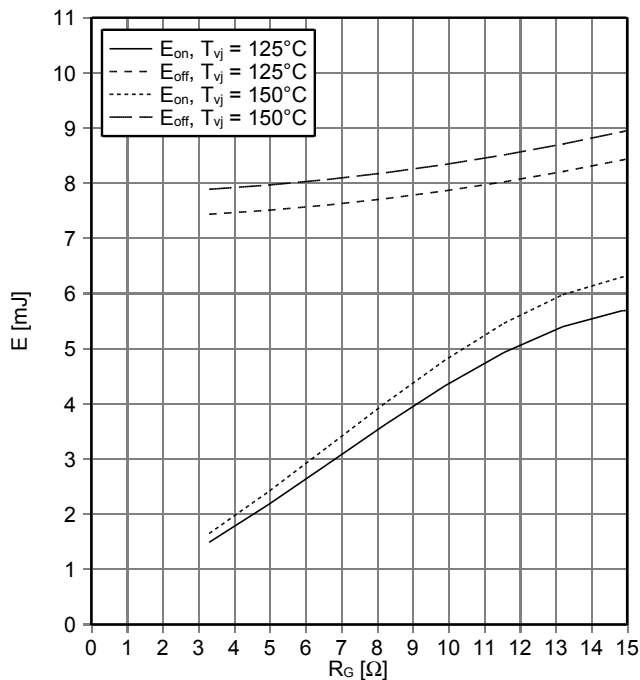


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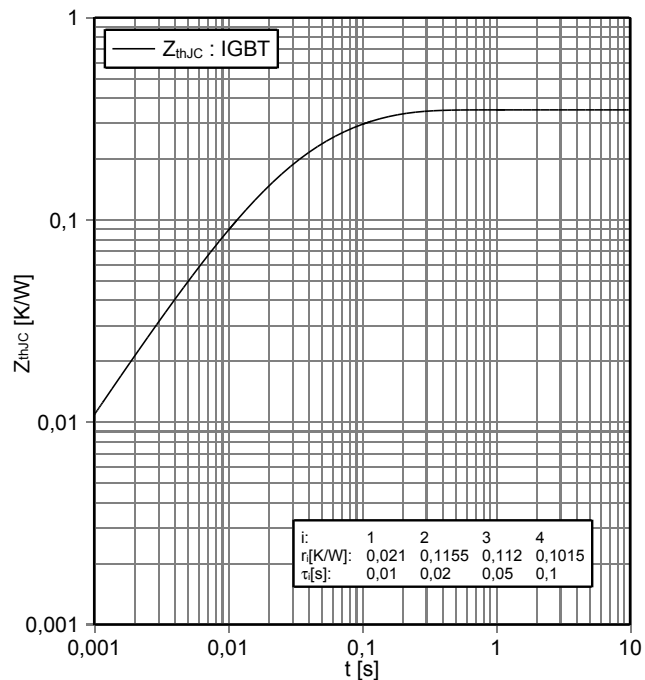
开关损耗 IGBT, 逆变器 (典型)  
switching losses IGBT, Inverter (typical)

$E_{on} = f(R_G), E_{off} = f(R_G)$   
 $V_{GE} = \pm 15\text{ V}, I_C = 150\text{ A}, V_{CE} = 300\text{ V}$



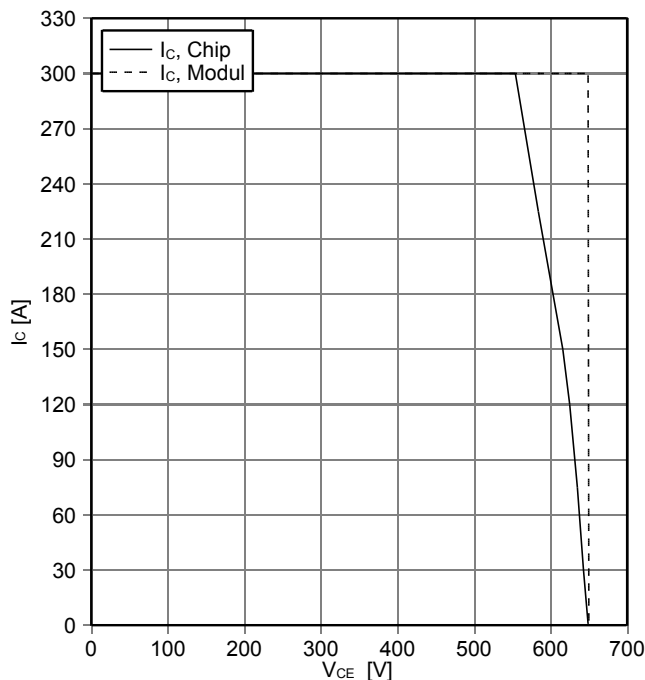
瞬态热阻抗 IGBT, 逆变器  
transient thermal impedance IGBT, Inverter

$Z_{thJC} = f(t)$



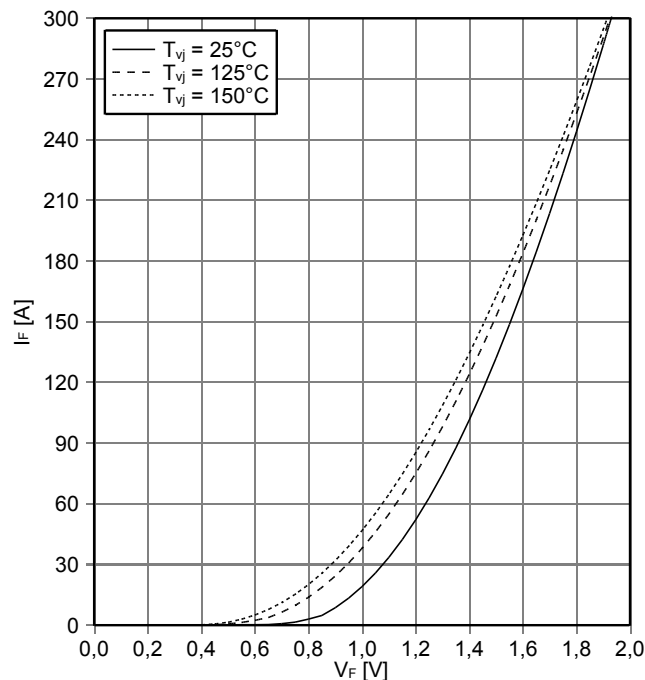
反偏安全工作区 IGBT, 逆变器 (RBSOA)  
reverse bias safe operating area IGBT, Inverter (RBSOA)

$I_C = f(V_{CE})$   
 $V_{GE} = \pm 15\text{ V}, R_{Goff} = 3.3\ \Omega, T_{vj} = 150^\circ\text{C}$



正向偏压特性 二极管, 逆变器 (典型)  
forward characteristic of Diode, Inverter (typical)

$I_F = f(V_F)$



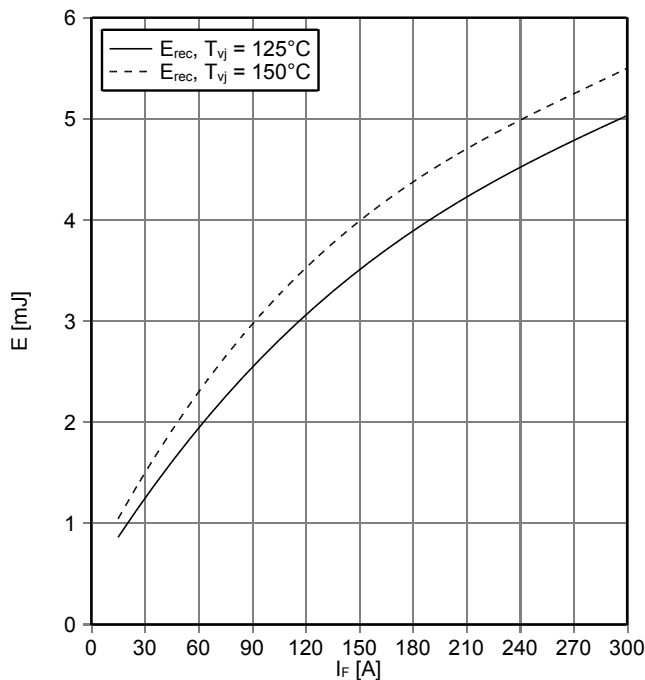
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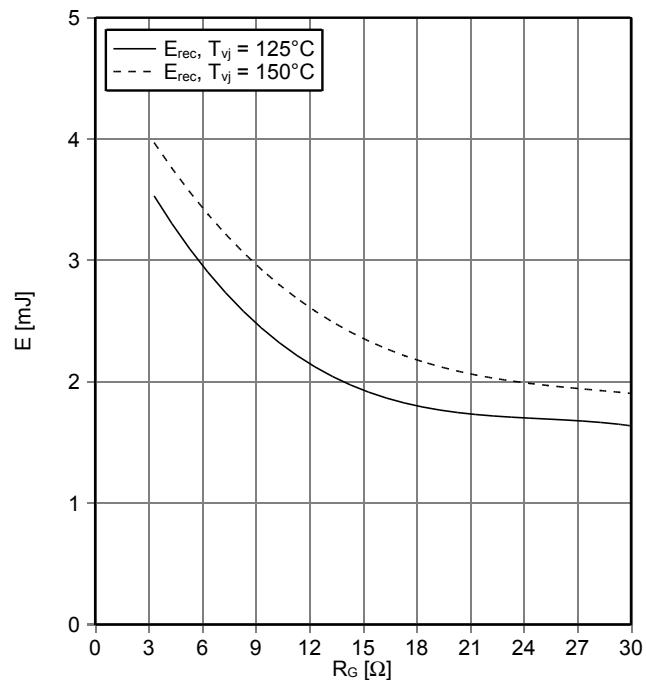
开关损耗 二极管,逆变器 (典型)  
switching losses Diode, Inverter (typical)

$E_{rec} = f(I_F)$   
 $R_{Gon} = 3.3 \Omega, V_{CE} = 300 V$



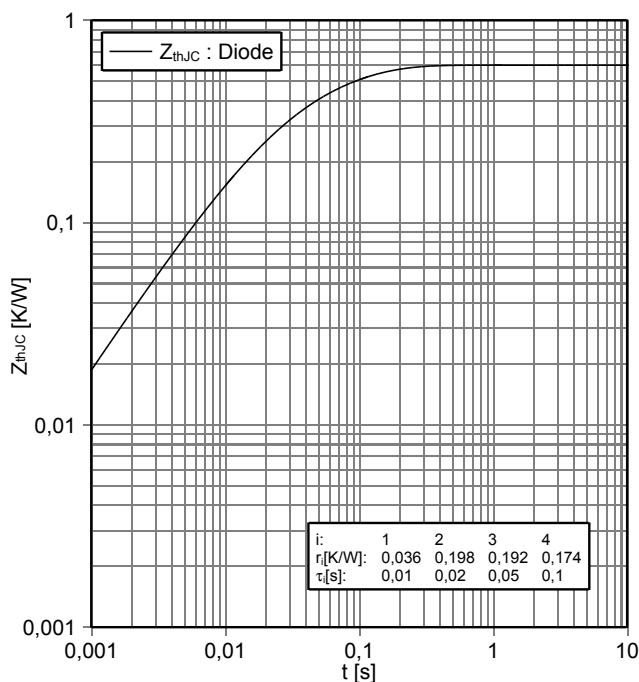
开关损耗 二极管,逆变器 (典型)  
switching losses Diode, Inverter (typical)

$E_{rec} = f(R_G)$   
 $I_F = 150 A, V_{CE} = 300 V$



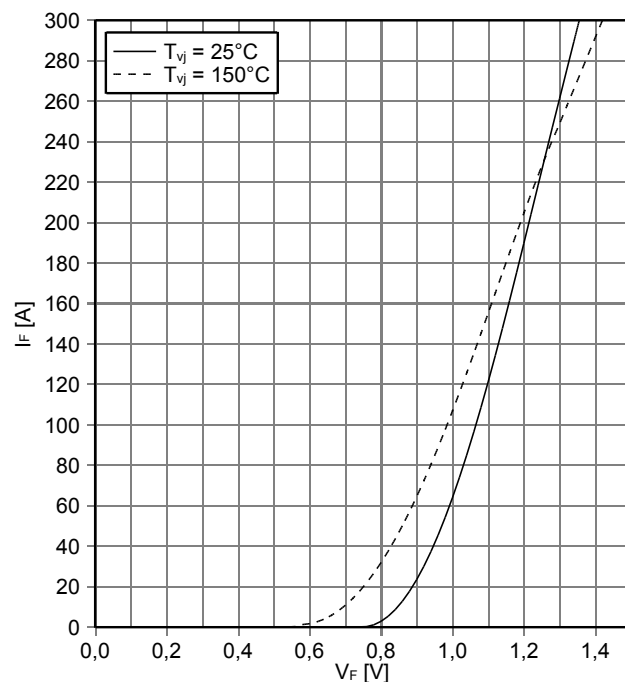
瞬态热阻抗 二极管,逆变器  
transient thermal impedance Diode, Inverter

$Z_{thJC} = f(t)$



正向偏压特性 二极管,整流器 (典型)  
forward characteristic of Diode, Rectifier (typical)

$I_F = f(V_F)$

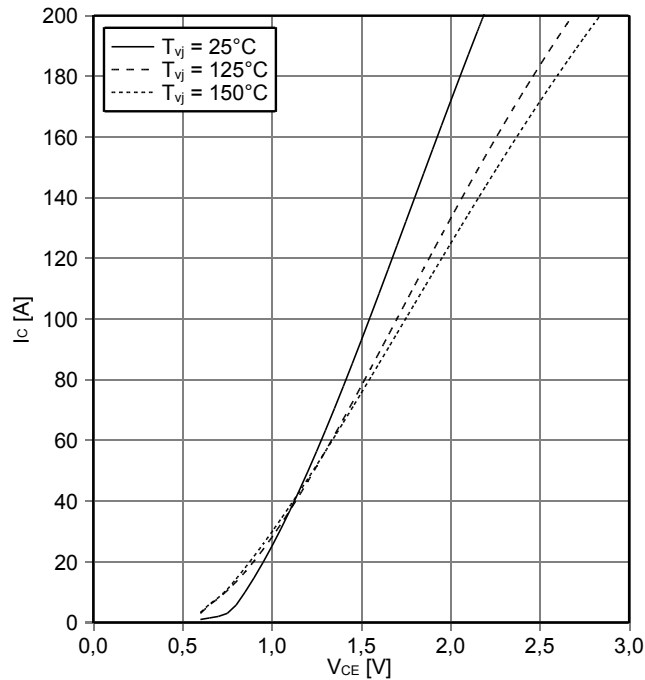


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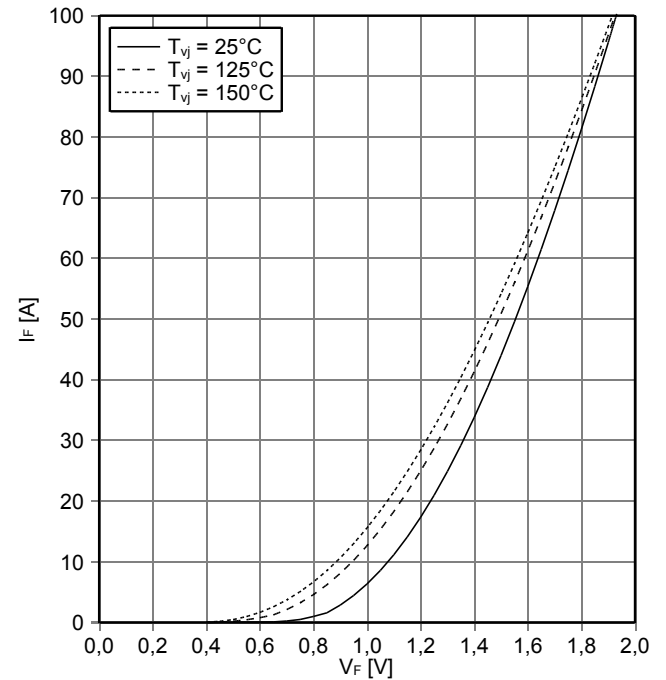
输出特性 IGBT, 制动-斩波器 (典型)  
output characteristic IGBT, Brake-Chopper (typical)

$I_C = f(V_{CE})$   
 $V_{GE} = 15\text{ V}$



正向偏压特性 二极管, 制动-斩波器 (典型)  
forward characteristic of Diode, Brake-Chopper (typical)

$I_F = f(V_F)$



负温度系数热敏电阻 温度特性  
NTC-Thermistor-temperature characteristic (typical)

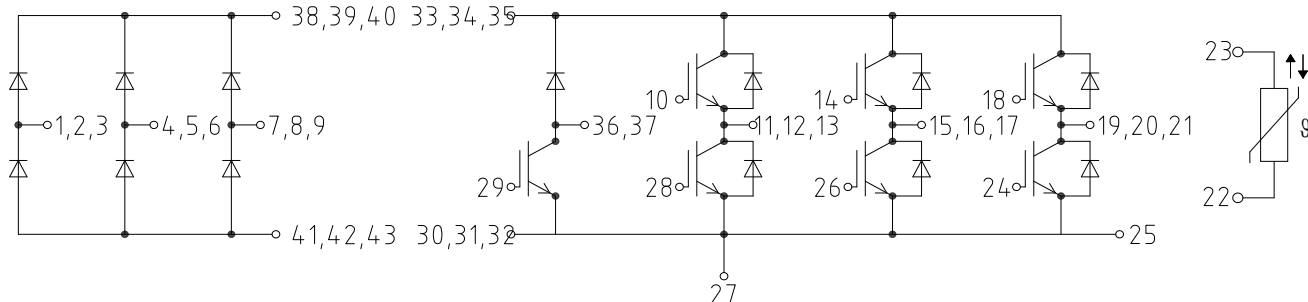
$R = f(T)$



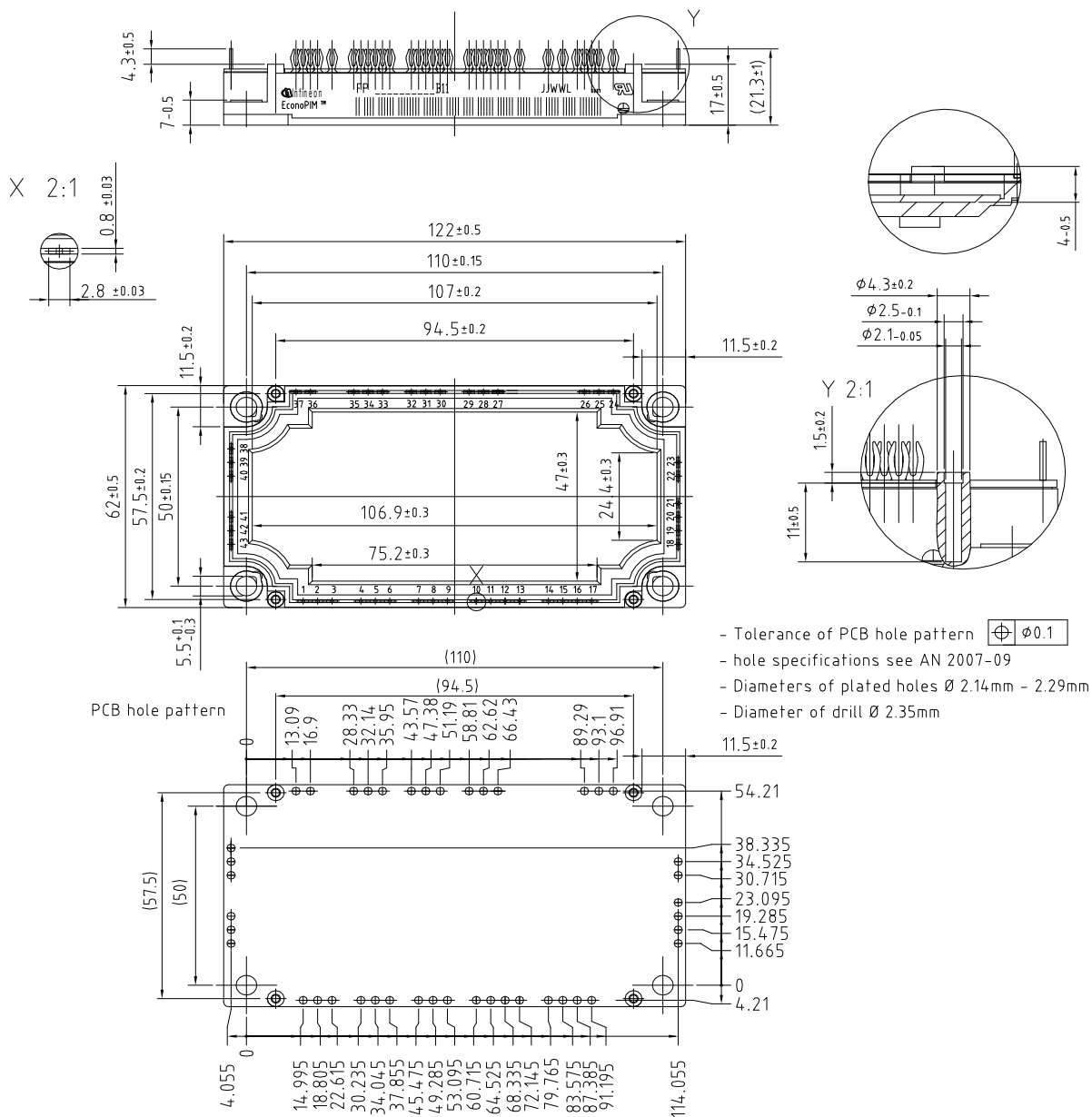
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接线图 / circuit\_diagram\_headline



封装尺寸 / package outlines



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**初步数据  
Preliminary Data**

**使用条件和条款**

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